

**SuperMOS – PDFN3X3-8L 30V BV<sub>DSS</sub>, 4mΩ R<sub>DS(on)</sub>, N-channel MOSFET**

**1. Description**

The ESN7534 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R<sub>DS(ON)</sub> with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESN7534 is Pb-free.

**2. Features**

- 30V, R<sub>DS(ON)</sub>=4.0mΩ(TYP.) @V<sub>GS</sub>=10V
- R<sub>DS(ON)</sub>=6.5mΩ(TYP.) @V<sub>GS</sub>=4.5V
- Use trench MOSFET technology
- High density cell design for low R<sub>DS(on)</sub>
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

**3. Applications**


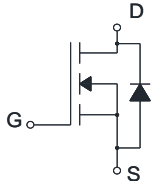
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

**100% UIS TESTED!**

**4. Ordering Information**

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ESN7534	PDFN3X3-8L	ESN7534/lot	Halogen free	Tape & Reel	5,000 PCS	UL 94V-0	13 inches

**5. Pin Configuration and Functions**

Pin	Function	Outline	Circuit Diagram
4	Gate		
1/2/3	Source		
5/6/7/8	Drain		

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$BV_{DSS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	45
		$T_C=75^\circ\text{C}$	35
Maximum Power Dissipation	$P_D$	$T_C=25^\circ\text{C}$	30
		$T_C=75^\circ\text{C}$	18
Pulsed Drain Current <sup>a</sup>	$I_{DM}$	180	A
Operating Junction Temperature	$T_J$	150	°C
Lead Temperature	$T_L$	260	°C
Storage Temperature Range	$T_{stg}$	-55 to 150	°C

#### Thermal resistance ratings

Single Operation				
Parameter		Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10 \text{ s}$	$R_{\theta JA}$	40	°C/W
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	4.2	

Note:

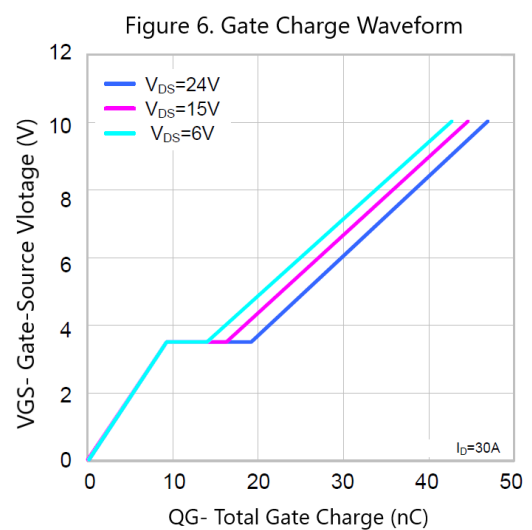
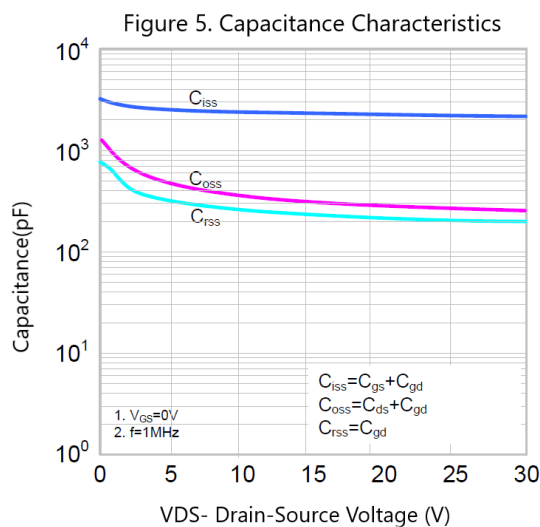
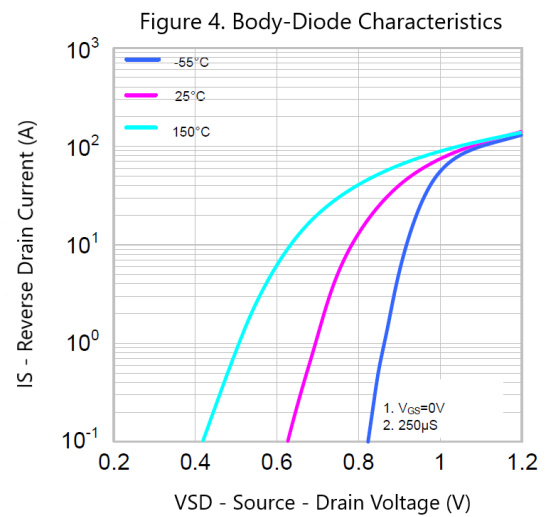
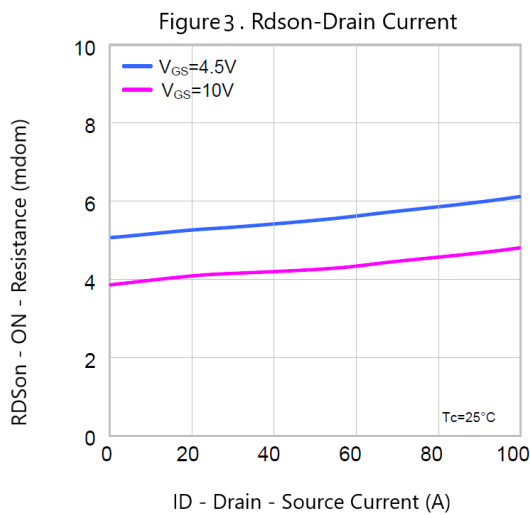
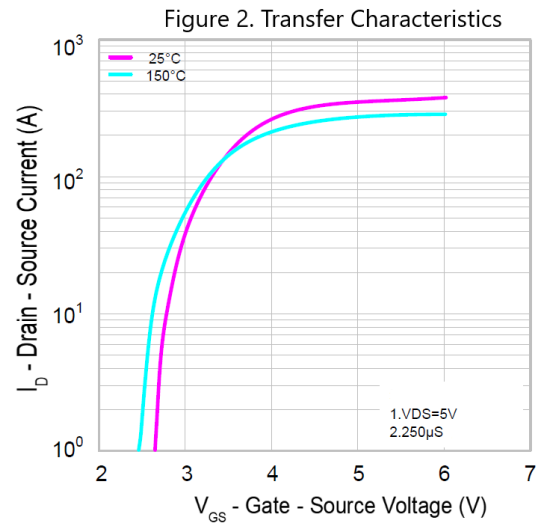
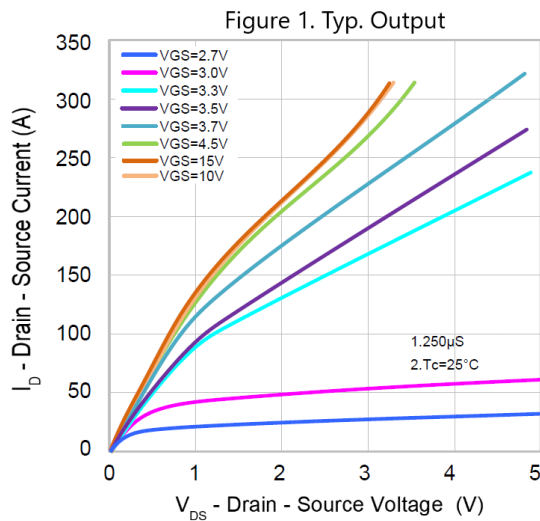
a: Repetitive rating, pulse width limited by junction temperature,  $t_p=10\mu\text{s}$ , Duty Cycle=1%

## Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$			1.0	$\mu A$
Gate-to-source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.75	2.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		4.0	7.5	m $\Omega$
		$V_{GS}=4.5V, I_D=16A$		6.5	9.5	
Forward Trans conductance	$g_{FS}$	$V_{DS}=5.0V, I_D=10A$			80	S
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, f=1MHz,$ $V_{DS}=25V$		2200		pF
Output Capacitance	$C_{OSS}$			275		
Reverse Transfer Capacitance	$C_{RSS}$			242		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=24V,$ $I_D=30A$		48		nC
Gate-to-Source Charge	$Q_{GS}$			8.8		
Gate-to-Drain Charge	$Q_{GD}$			10.0		
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=4.5V, V_{DS}=20V,$ $I_D=20A, R_G=1.8\Omega$		12.5		ns
Rise Time	$t_r$			90		
Turn-Off Delay Time	$t_{d(OFF)}$			142		
Fall Time	$t_f$			85		
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=1.0A$		0.75	1.5	V

## 7. Typical Characteristic



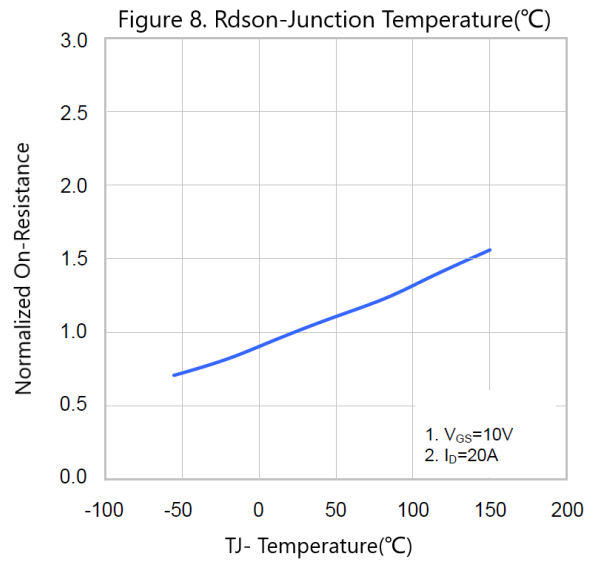
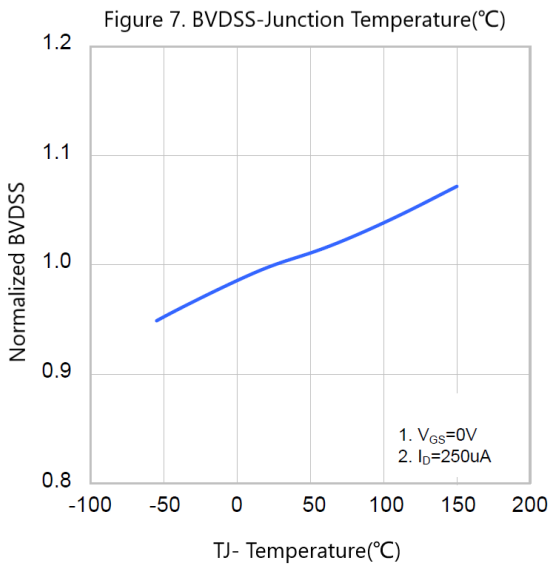


Figure 9. Maximum Safe Operation Area

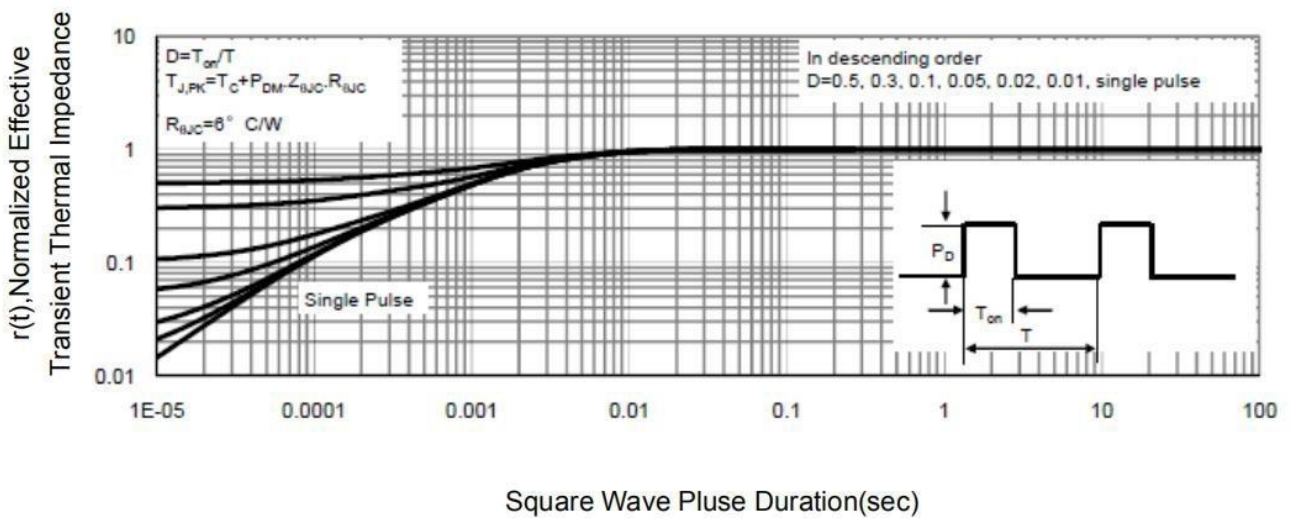
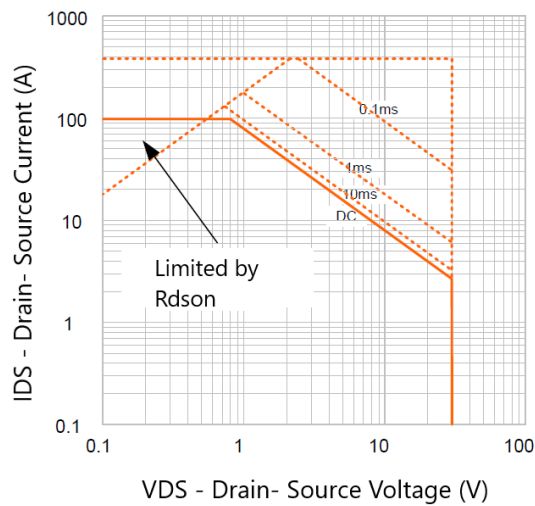
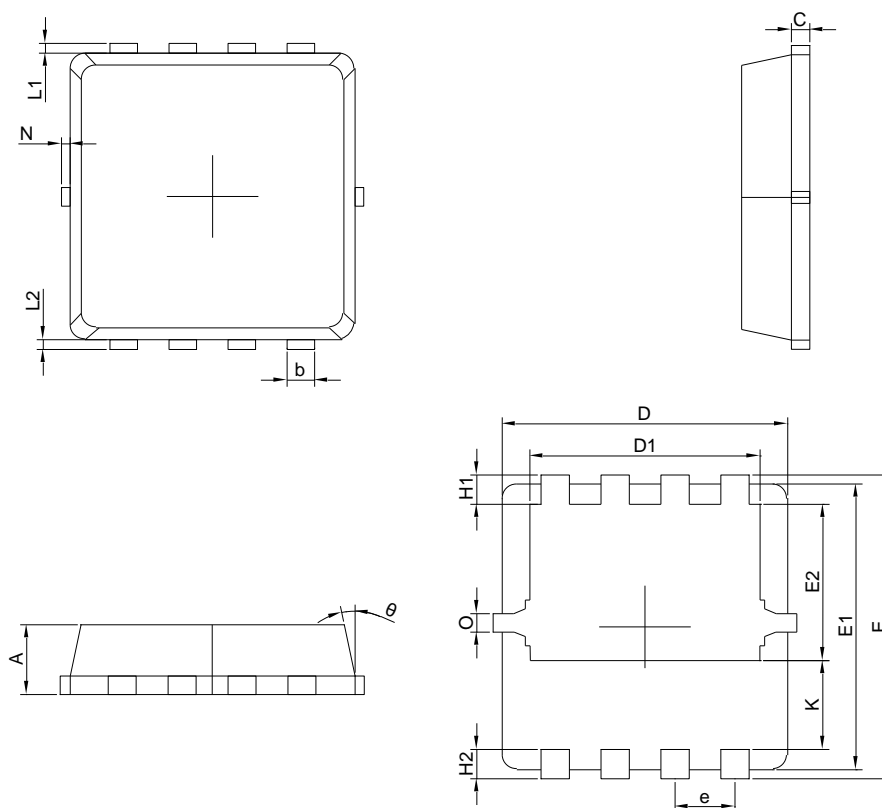


Figure 10 Normalized Maximum Transient Thermal Impedance

8. Dimension (PDFN3X3-8L)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.65	0.75	0.85	e	0.65 BSC.		
b	0.25	0.30	0.35	H1	0.21	0.31	0.41
C	0.15	0.20	0.25	H2	0.30	0.40	0.50
D	3.00	3.10	3.20	K	0.78	0.88	0.98
D1	2.40	2.50	2.60	L1/L2	0.10 REF.		
E	3.20	3.30	3.40	theta	11°	12°	13°
E1	3.00	3.10	3.20	N	0	-	0.15
E2	1.60	1.70	1.80	O	0.2 REF.		

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